

Chien-Min Cheng

List of Publications by Year in descending order

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38
papers

380
citations

933447

10
h-index

794594

19
g-index

38
all docs

38
docs citations

38
times ranked

335
citing authors

#	ARTICLE	IF	CITATIONS
1	Promoting Relaxation Using Monaural Beats With Ultralow-Frequency Inaudible Sounds: An Empirical Case Study. <i>IEEE Access</i> , 2022, 10, 50807-50818.	4.2	2
2	Dielectric, Piezoelectric, and Vibration Properties of the LiF-Doped (Ba _{0.95} Ca _{0.05})(Ti _{0.93} Sn _{0.07})O ₃ Lead-Free Piezoceramic Sheets. <i>Materials</i> , 2018, 11, 182.	2.9	2
3	Schottky Emission Distance and Barrier Height Properties of Bipolar Switching Gd:SiO _x RRAM Devices under Different Oxygen Concentration Environments. <i>Materials</i> , 2018, 11, 43.	2.9	25
4	Bipolar switching properties and electrical conduction mechanism of manganese oxide RRAM devices. <i>Ceramics International</i> , 2017, 43, S253-S257.	4.8	22
5	Influence of Thermal Annealing Treatment on Bipolar Switching Properties of Vanadium Oxide Thin-Film Resistance Random-Access Memory Devices. <i>Journal of Electronic Materials</i> , 2017, 46, 2147-2152.	2.2	7
6	Characteristics improvement of Li _{0.058} (K _{0.480} Na _{0.535}) _{0.966} (Nb _{0.9} Ta _{0.1})O ₃ piezoelectric ceramics by LiF additions. <i>Integrated Ferroelectrics</i> , 2016, 168, 53-60.		
7	The inferences of ZnO additions for LKNNT lead-free piezoelectric ceramics. <i>Integrated Ferroelectrics</i> , 2016, 168, 61-68.	0.7	2
8	Nonvolatile transparent manganese oxide thin film resistance random access memory devices. <i>Japanese Journal of Applied Physics</i> , 2014, 53, 08NL03.	1.5	4
9	Electrical and Ferroelectric Properties of the Bi _{3.9} La _{0.1} Ti _{2.9} V _{0.1} O ₁₂ (BLTV) Thin Films. <i>Integrated Ferroelectrics</i> , 2014, 158, 83-89.	0.7	0
10	Ferroelectric, Dielectric, and Physical Characteristics of (Ba _{1-x} Sr _x)(Ti _{1-y} Zr _y)O ₃ Thin Films. <i>Integrated Ferroelectrics</i> , 2013, 143, 32-39.	0.7	2
11	One-Transistor-Capacitor (1TC) Structure of Non-Volatile Ferroelectric RAM Using 0.95(Na _{0.5} Bi _{0.5})TiO ₃ -0.05BaTiO ₃ Thin Film. <i>Integrated Ferroelectrics</i> , 2013, 143, 10-16.	0.7	1
12	Bipolar resistive switching properties in transparent vanadium oxide resistive random access memory. <i>Ceramics International</i> , 2013, 39, S729-S732.	4.8	14
13	Fabrication and Electrical Characteristics of Metal-Ferroelectric Ba(Zr _{0.1} Ti _{0.9})O ₃ Film in Insulator-Silicon Structure. <i>Integrated Ferroelectrics</i> , 2013, 143, 40-46.	0.7	1
14	Influence of Lithium and Potassium Doping on Structure and Electrical Characteristics of Li _x (K _y Na _{1-y}) _{1-x} (Nb _{0.9} Ta _{0.06} Sb _{0.04})O ₃ Lead-Free Piezoelectric Ceramics. <i>Japanese Journal of Applied Physics</i> , 2012, 51, 035801.	1.5	2
15	EFFECT OF ANNEALING TREATMENT ON FERROELECTRIC AND ELECTRICAL CHARACTERISTICS OF Bi ₄ XLaXTi ₃ O ₁₂ THIN FILMS ON ITO/GLASS SUBSTRATE. <i>International Journal of Modern Physics Conference Series</i> , 2012, 06, 552-556.	0.7	0
16	IMPROVEMENT ON CHARACTERISTICS OF FERROELECTRIC THIN FILMS USING SUPERCRITICAL CARBON DIOXIDE FLUID TREATMENT. <i>International Journal of Modern Physics Conference Series</i> , 2012, 06, 104-108.	0.7	0
17	FERROELECTRIC PROPERTIES OF CaBi ₄ Ti ₄ O ₁₅ THIN FILMS ON ITO/GLASS SUBSTRATES PREPARED BY SOL-GEL TECHNOLOGY. <i>International Journal of Modern Physics Conference Series</i> , 2012, 06, 91-97.	0.7	0
18	Electrical and Physical Characteristics of Vanadium-Doped Bi ₄ Ti ₃ O ₁₂ Ferroelectric Thin Films after Rapid Thermal Annealing. <i>Ferroelectrics</i> , 2012, 435, 55-61.	0.6	0

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19	Effect of Sintering Temperature on Piezoelectric and Ferroelectric Properties of Lead-Free Piezoelectric Ta-modified $(K_{0.5}Na_{0.5})NbO_3$ Ceramics. <i>Ferroelectrics</i> , 2012, 435, 46-54.	0.6	0
20	Solution-based fabrication and electrical properties of $CaBi_4Ti_4O_{15}$ thin films. <i>Ceramics International</i> , 2012, 38, S87-S90.	4.8	9
21	Electric aging behavior of lead-free $Li_{0.06}(K_{0.48}Na_{0.52})_{0.94}(Nb_{0.86}Ta_{0.08}Sb_{0.06})O_3$ piezoelectric ceramics improved by pre-calcined method. <i>Ceramics International</i> , 2012, 38, S335-S338.	4.8	3
22	A Low Profile Dual Band Antenna for Implanted ZigBee Based Biosensors. , 2011, , .		0
23	The influence of lanthanum doping on the physical and electrical properties of BTV ferroelectric thin films. <i>Applied Physics A: Materials Science and Processing</i> , 2011, 103, 1173-1177.	2.3	7
24	Develop CPW-FED monopole broadband implantable antennas on the high dielectric constant ceramic substrates. <i>Microwave and Optical Technology Letters</i> , 2010, 52, 2136-2139.	1.4	9
25	Development of Nonsuperstrate Implantable Low-Profile CPW-Fed Ceramic Antennas. <i>IEEE Antennas and Wireless Propagation Letters</i> , 2010, 9, 599-602.	4.0	72
26	Develop Quad-Band (1.57/2.45/3.5/5.2 GHz) Bandpass Filters on the Ceramic Substrate. <i>IEEE Microwave and Wireless Components Letters</i> , 2010, 20, 268-270.	3.2	77
27	Develop dual-band CPW asymmetric monopole antennas on the Aluminum Oxide substrates. , 2009, , .		1
28	Design a new structure 2.4 GHz/5.2 GHz dual-band bandpass filters on the $MgTa_{1.5}Nb_{0.5}O_6$ ceramic. <i>Microwave and Optical Technology Letters</i> , 2009, 51, 1085-1087.	1.4	1
29	Large memory window in the vanadium doped $Bi_4Ti_3O_{12}$ thin films. <i>Applied Physics A: Materials Science and Processing</i> , 2009, 97, 919-923.	2.3	7
30	Fabrication of a new-type wideband bandpass filter on the $MgTa_{1.5}Nb_{0.5}O_6$ ceramic substrate. <i>Microwave and Optical Technology Letters</i> , 2008, 50, 3223-3225.	1.4	2
31	The Characteristics Development of excess $Bi_{2-x}O_{3-x}$ -doped $0.65Bi_{0.5}K_{0.5}TiO_3+0.35BaTiO_3$ Ceramics. , 2007, , .		0
32	Fabricate Wide-Band Microstrip Line T-shaped Antenna on the Al_2O_3 Substrate. , 2007, , .		0
33	Fabricate Modified Dual-Band Parallel-Coupled Microstrip Filters on the Al_2O_3 Ceramic Substrate. , 2007, , .		1
34	Sintering and compositional effects on the microwave dielectric characteristics of $Mg(Ta_{1-x}Nb_x)_2O_6$ ceramics. <i>Journal of the European Ceramic Society</i> , 2006, 26, 1357-1363.	2.0	13
35	Microwave dielectric characteristics of $Mg(Ta_{1-x}Nb_x)_2O_6$ ceramics. <i>Materials Research Bulletin</i> , 2006, 41, 1357-1363.	5.2	21
36	The sintering and microwave dielectric characteristics of $MgTa_{1.5}Nb_{0.5}O_6$ ceramics. <i>Journal of the European Ceramic Society</i> , 2005, 25, 2849-2852.	5.7	16

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37	The sintering and microwave dielectric characteristics of MgO-CaO-Al ₂ O ₃ -SiO ₂ glass-fluxed Ba(Mg _{1/3} Ta _{2/3})O ₃ ceramics. Materials Letters, 2003, 57, 1471-1476.	2.6	10
38	Sintering BaTi ₄ O ₉ /Ba ₂ Ti ₉ O ₂₀ -based ceramics by glass addition. Journal of the European Ceramic Society, 2000, 20, 1061-1067.	5.7	45